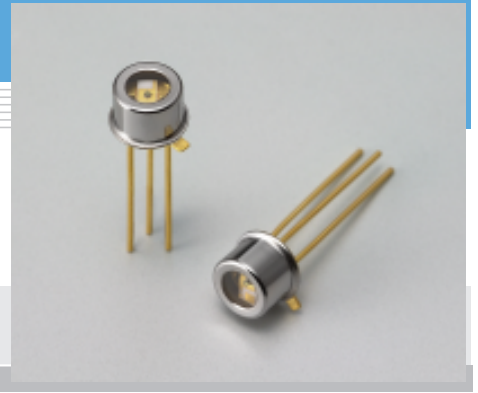


InGaAs APD

G8931-04

Time response characteristics compatible with SONET and G/GE-PON



The G8931-04 is an InGaAs APD that delivers a high-speed response of 2.5 Gbps required for trunk line optical fiber communications such as SONET (synchronous optical network), G-PON (gigabit-capable passive optical network) and GE-PON (gigabit ethernet-passive optical network).

Features

- High-speed response: 2.5 Gbps
- Low dark current
- Low capacitance
- Active area: $\phi 0.04$ mm
- High sensitivity

Applications

- Optical fiber communications
- High-speed data links

General ratings

Parameter	Symbol	Value	Unit
Active area	-	$\phi 0.04$	mm

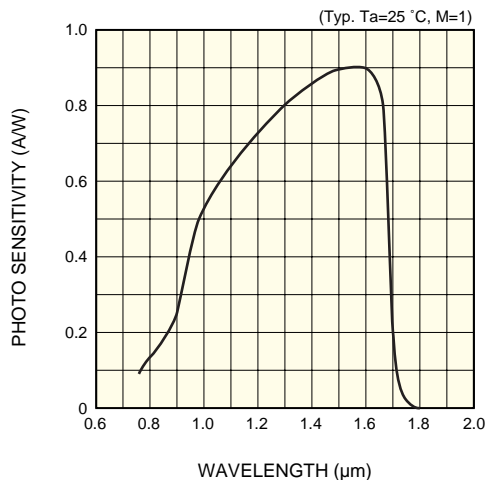
Absolute maximum ratings

Parameter	Symbol	Value	Unit
Forward current	I_F	2	mA
Reverse current	I_R	2	mA
Operating temperature	T_{opr}	-40 to +85	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^{\circ}\text{C}$

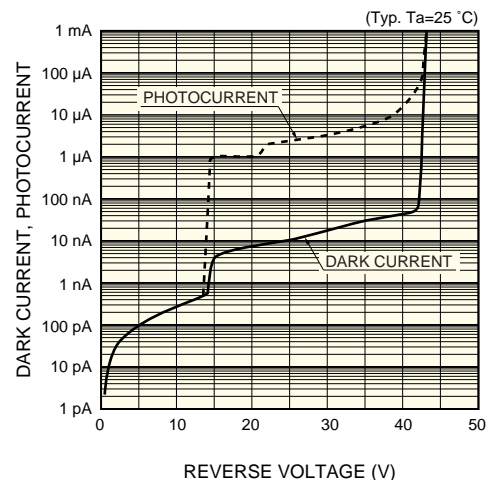
Electrical and optical characteristics ($T_a=25^{\circ}\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Spectral response range	λ		-	0.95 to 1.7	-	μm
Peak sensitivity wavelength	λ_p		-	1.55	-	μm
Photo sensitivity	S	$\lambda=1.55 \mu\text{m}$, $M=1$	0.8	0.9	-	A/W
Breakdown voltage	V_{BR}	$I_D=100 \mu\text{A}$	40	-	60	V
Temperature coefficient of V_{BR}	Γ	-40 to +85 $^{\circ}\text{C}$	-	0.11	0.16	V/ $^{\circ}\text{C}$
Dark current	I_D	$V_R=V_{BR} \times 0.9$	-	40	65	nA
Cut-off frequency	f_c	$M=10$	3	4	-	GHz
Terminal capacitance	C_t	$V_R=V_{BR} \times 0.9$ $f=1 \text{ MHz}$	-	0.35	0.45	pF

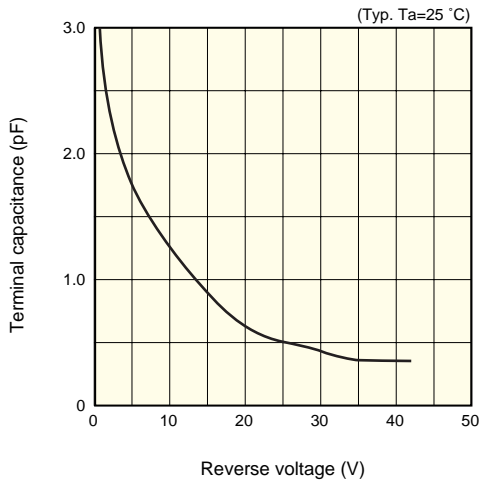
Spectral response



Dark current vs. reverse voltage

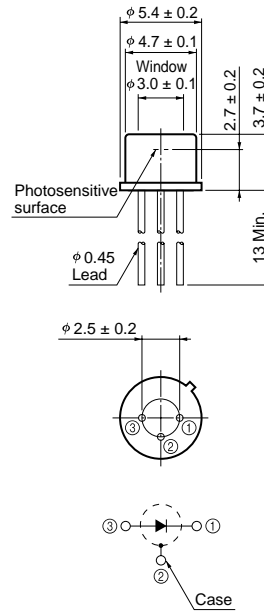


■ Terminal capacitance vs. reverse voltage



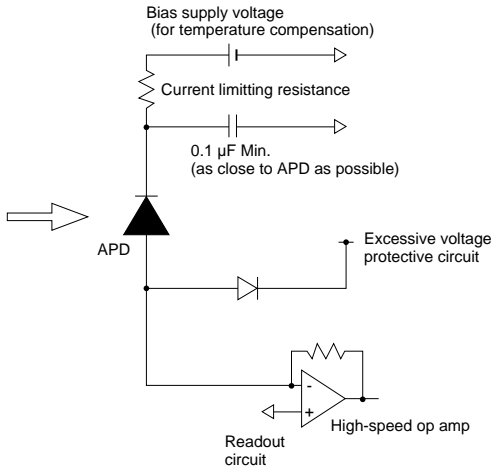
KAPDB0124EA

■ Dimensional outline (unit: mm)



KAPDA0034EA

■ Peripheral circuit example of APD



KAPDC0005EC

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HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81) 53-434-3311, Fax: (81) 53-434-5184, www.hamamatsu.com

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 08152-3750, Fax: (49) 08152-2658

France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1/E, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741